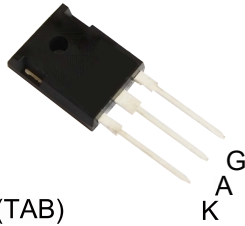


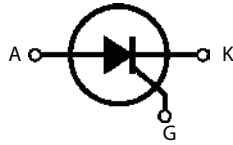
STYN1265

Discrete Thyristors(SCRS)



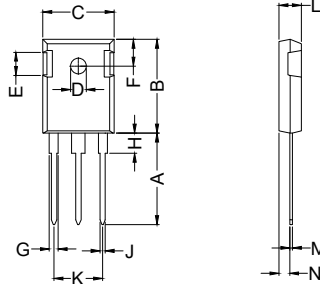
A(TAB)

K=Cathode, A=Anode, G=Gate



Dimensions TO-247AD

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.620	0.640
ØD	3.15	3.65	0.124	0.144
E	4.32	5.49	0.170	0.216
F	5.40	6.30	0.213	0.248
G	1.65	2.18	0.065	0.086
H	3.80	4.50	0.150	0.177
J	1.00	1.40	0.039	0.055
K	10.80	11.10	0.425	0.437
L	4.70	5.30	0.185	0.209
M	0.40	0.80	0.016	0.031
N	1.50	2.49	0.059	0.098

	V_{RRM} V	V_{RSM} V
STYN1265	1200	1300

Symbol	Test Conditions		Maximum Ratings	Unit
I_{TRMS} I_{TAVM}	$T_{VJ}=T_{VJM}$ $T_C=75^{\circ}C$; 180° sine		65 41	A
I_{TSM}	$T_{VJ}=45^{\circ}C$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	520 560	A
	$T_{VJ}=T_{VJM}$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	460 500	
I^2t	$T_{VJ}=45^{\circ}C$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1350 1300	A ² s
	$T_{VJ}=T_{VJM}$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1050 1030	
$(di/dt)_{cr}$	$T_{VJ}=T_{VJM}$ $f=50Hz$, $t_p=200\mu s$ $V_D=2/3V_{DRM}$ $I_G=0.3A$ $di_G/dt=0.3A/\mu s$	repetitive, $I_T=40A$	150	A/ μs
		non repetitive, $I_T=I_{TAVM}$	500	
$(dv/dt)_{cr}$	$T_{VJ}=T_{VJM}$; $R_{GK}=\infty$; method 1 (linear voltage rise)	$V_{DR}=2/3V_{DRM}$	1000	V/ μs
P_{GM}	$T_{VJ}=T_{VJM}$ $I_T=I_{TAVM}$	$t_p=30\mu s$ $t_p=300\mu s$	10 5	W
P_{GAV}			0.5	W
V_{RGM}			10	V
T_{VJ} T_{VJM} T_{stg}			-40...+140 140 -40...+125	$^{\circ}C$
V_{ISOL}	50/60Hz, RMS	$t=1minute$, leads-to-tab	2500	V~
M_d F_c	Mounting torque (M3) Mounting force with clip		0.8...1.2 20...120	Nm N
Weight			6	g

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STYN1065

Discrete Thyristors(SCRS)

Symbol	Test Conditions	Characteristic Values	Unit
I_R, I_D	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	5	mA
V_T	$I_T=80A; T_{VJ}=25^{\circ}C$	1.64	V
V_{TO}	For power-loss calculations only ($T_{VJ}=125^{\circ}C$)	0.85	V
r_T		11	m Ω
V_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
I_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	100 200	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.2	V
I_{GD}		10	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=10\mu s;$ $I_G=0.3A; di_G/dt=0.3A/\mu s$	150	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	100	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.3A; di_G/dt=0.3A/\mu s$	2	μs
R_{thJC}	DC current	0.62	K/W
R_{thJH}	DC current	0.82	K/W
a	Max. acceleration, 50 Hz	50	m/s ²

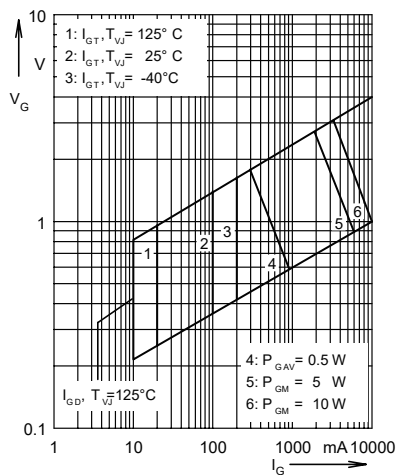


Fig. 1 Gate trigger range

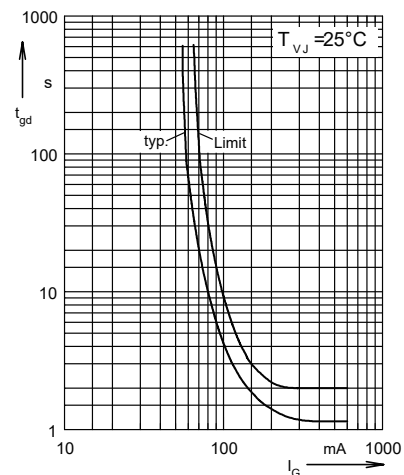


Fig. 2 Gate controlled delay time t_{gd}



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Discrete Thyristors(SCRS)

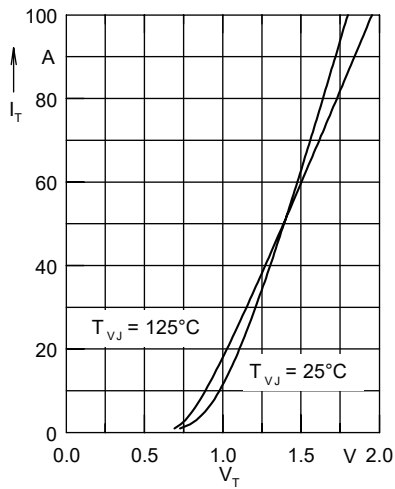


Fig.3 Forward characteristics

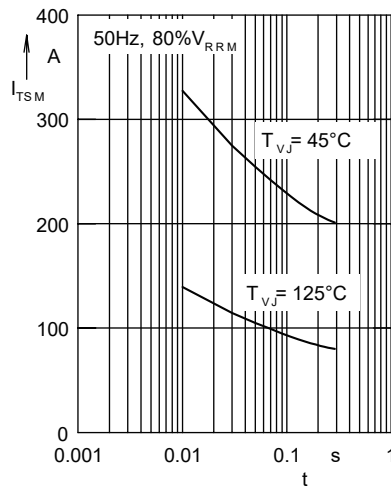


Fig.4 Surge overload current
 I_{TSM} : crest value, t : duration

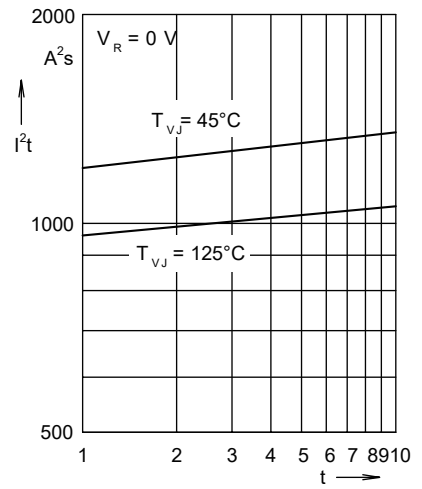


Fig.5 I^2t versus time (1-10 ms)

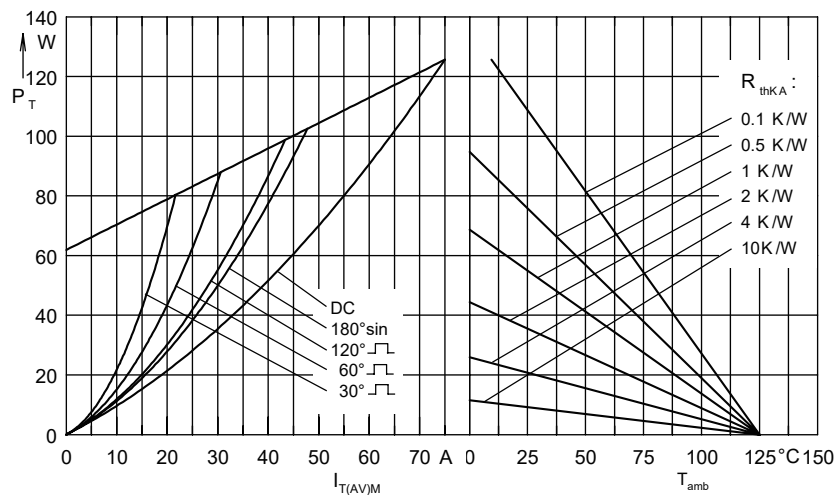


Fig.6 Power dissipation versus forward current and ambient temperature

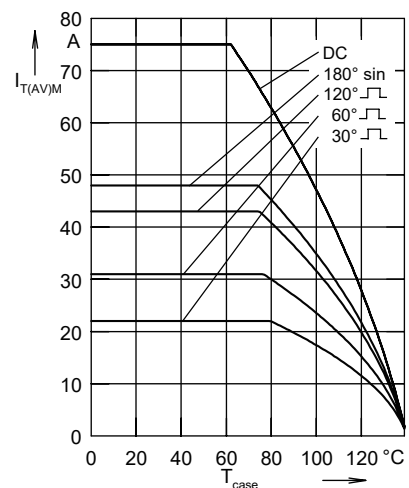
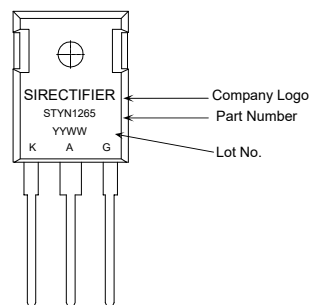


Fig.7 Max. forward current at case temperature

MARKING



ORDERING INFORMATION

Part Number	Package	Shipping	Marking Code
STYN1265	TO-247AD	30pcs / Tube	STYN1265

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